

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

**COPY**

In re the Application of

Hiroyuki ABE et al.

Group Art Unit: 2814

Application No.: 08/930,449

Examiner: S. Rao

Filed: October 7, 1997

Docket No.: JAO 39514

For: HIGH ENERGY SUPPLY APPARATUS, METHOD OF  
FORMING CRYSTALLINE FILM AND METHOD OF  
MANUFACTURING THIN FILM ELECTRONIC DEVICE

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**AMENDMENT PRIOR TO CONTINUED EXAMINATION**

Director of the U.S. Patent and Trademark Office  
Washington, D.C. 20231

Sir:

Prior to continued examination of the above-identified application, please amend the application as follows.

**IN THE CLAIMS:**

Please amend claims 1, 12, 20, 25, 30, 35, 40, 46 and 56 as follows:

1. (Three Times Amended) A method of forming a crystalline film, comprising [the steps of]:
- forming a thin film having a surface on a substrate; and
- crystallizing at least a surface layer of the thin film by [selectively] applying energy to the surface of the thin film, [such that] at least the surface layer of the thin film is melted by the applied energy and crystallized by cooling solidification under a hydrogen-containing atmosphere,

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